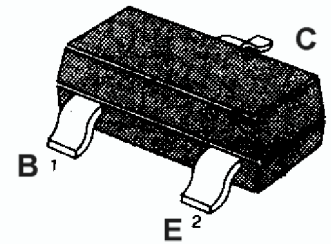


APPLICATION: General purpose applications.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	-80	V
Collector-emitter voltage	V _{CEO}	-65	V
Emitter-base voltage	V _{EBO}	-6	V
Collector current	I _c	-100	mA
Collector Power Dissipation	P _c	310	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

SOT-23



1.Base 2 .Emitter 3 .Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	110		800		V _{CE} = -5 V, I _c = -2mA
Collector Cut-off Current	I _{CB0}			-0.015	μA	V _{CB} = -30V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.015	μA	V _{EB} = -4V, I _c =0
Collector-Base Breakdown Voltage	BV _{CB0}	-80			V	I _c = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-65			V	I _c = -1 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-6			V	I _E = -0.1mA, I _c =0
Base-Emitter Voltage	V _{BE}			-0.75	V	V _{CE} = -5V, I _c = -2 mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.3	V	I _c = -100mA, I _B = -0.5mA
				-0.65		I _c = -100 mA, I _B = -5 mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		-0.7		V	I _c = -100 mA, I _B = -0.5 mA
			-0.9			I _c = -100 mA, I _B = -5 mA
Gain bandwidth product	f _T		300		MHz	I _c = -10mA, V _{CE} =-5V, f=100MHz
Common Base Output Capacitance	C _{ob}			6	PF	V _{CB} = -10V, I _E =0, f= 1 MHz
Noise Figure	N _F		2	10	dB	V _{CE} = -5 V,I _c = -0.2 mA,f= 1 kHz, R _g = 2kΩ

h_{FE} Classification And Marking

Print Mark

Classification	A	B	C
h _{FE}	110~220	200~450	420~800